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## Amendments to the Claims:

The Listing of Claims will replace all prior versions, and listings, of claims in the application.

## Listing of the Claims:

1. (Previously Presented) A method of forming a cell pad contact hole on an integrated circuit, comprising:

forming adjacent gates on an integrated circuit substrate having a source/drain region extending between the gates;

forming gate spacers on facing sidewalls of the adjacent gates;

forming a cell pad contact hole aligned to the gates and gate spacers that exposes the source/drain region in the integrated circuit substrate;

forming a first poly film in the cell pad contact hole;

forming a region in the source/drain region by ion-implanting through the first poly film; and

forming a second poly film on the first poly film that substantially fills the cell pad contact hole, wherein a concentration of dopants in the first poly film is lower than a concentration of dopants in the second poly film.

- 2. (Original) The method of Claim 1 wherein the gate spacers are formed from a nitride film.
- 3. (Original) The method of Claim 1 wherein the source/drain region comprises an N-type source/drain region overlapping the gates.
- 4. (Original) The method of Claim 1 further comprising forming an insulating film that planarizes undulations from the gates before forming a cell pad contact hole.



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- 5. (Original) The method of Claim 4 further comprising etching the first and second poly films to expose an upper surface of the insulating film.
- 6. (Original) The method of Claim 4 wherein forming the first poly film comprises conformably forming the first poly film in the cell pad contact hole.
- 7. (Original) The method of Claim 4 wherein the first poly film comprises an undoped poly film.
- 8. (Original) The method of Claim 4 wherein the first poly film comprises a doped poly film.
  - Canceled.
- 10 (Previously Presented) The method of Claim 4 wherein forming the first poly film comprises forming the first poly film to a thickness selected to provide a desired depth of the region formed by ion implanting.
- 11. (Original) The method of Claim 4 wherein forming the adjacent gates comprises:

forming a poly film of the gates on the integrated circuit substrate; forming a tungsten silicide (WSi) film of the gates on the poly film of the gates; and forming a nitride film of the gates on the tungsten silicide film.

12. (Original) The method of Claim 4 further comprising:

forming an additional insulating layer on the first poly film, the second poly film and the insulating layer;

forming a buried contact hole in the additional insulating layer that exposes an upper surface of the second poly film;

forming a contact poly film in the buried contact hole; and

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etching the contact poly film to expose an upper surface of the additional insulating layer.

## 13-31. (Canceled)

32. (Previously Presented) A method of forming a cell pad contact hole on an integrated circuit, comprising:

forming adjacent gates on an integrated circuit substrate and forming a source/drain region extending between the gates;

forming gate spacers on facing sidewalls of the adjacent gates;

forming a cell pad contact hole aligned to the gates and gate spacers that exposes the source/drain region in the integrated circuit substrate;

forming a first poly film in the cell pad contact hole;

forming a region in the source/drain region by ion-implanting through the first poly film; and

forming a second poly film on the first poly film that substantially fills the cell pad contact hole, wherein a concentration of dopants in the first poly film is lower than a concentration of dopants in the second poly film.

- 33. (Previously Presented) The method of Claim 32 wherein the gate spacers are formed from a nitride film.
- 34. (Previously Presented) The method of Claim 32 wherein the source/drain region comprises an N-type source/drain region overlapping the gates.
- 35. (Previously Presented) The method of Claim 32 further comprising forming an insulating film that planarizes undulations from the gates before forming a cell pad contact hole.

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- 36. (Previously Presented) The method of Claim 35 further comprising etching the first and second poly films to expose an upper surface of the insulating film.
- 37. (Previously Presented) The method of Claim 35 wherein forming the first poly film comprises conformably forming the first poly film in the cell pad contact hole.
- 38. (Previously Presented) The method of Claim 35 wherein the first poly film comprises an undoped poly film.
- 39. (Previously Presented) The method of Claim 35 wherein the first poly film comprises a doped poly film.
  - 40. Canceled.
- 41 (Previously Presented) The method of Claim 35 wherein forming the first poly film comprises forming the first poly film to a thickness selected to provide a desired depth of the region formed by ion implanting.
- 42. (Previously Presented) The method of Claim 35 wherein forming the adjacent gates comprises:

forming a poly film of the gates on the integrated circuit substrate; forming a tungsten silicide (WSi) film of the gates on the poly film of the gates; and forming a nitride film of the gates on the tungsten silicide film.

43. (Previously Presented) The method of Claim 35 further comprising: forming an additional insulating layer on the first poly film, the second poly film and the insulating layer;

forming a buried contact hole in the additional insulating layer that exposes an upper surface of the second poly film;

forming a contact poly film in the buried contact hole; and

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etching the contact poly film to expose an upper surface of the additional insulating layer.

44-45. Canceled.